



2SB1133

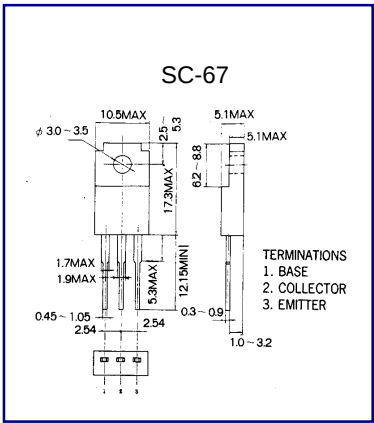
PNP EPITAXIAL SILICON TRANSISTOR

POWER AMPLIFIER
VERTICAL DEFLECTION OUTPUT



ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CE0}	-60	V
Emitter-Base voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-3	A
Collector Dissipation (T _c =25°C)	P _C	20	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -150V , I _E =0			-10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = -5V , I _C =0			-10	μA
DC Current Gain	h _{FE1}	V _{CE} = -2.0V , I _C =-1.0A	70		240	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =-3A , I _B =-0.3mA			-1.4	V
Current Gain Bandwidth Product	f _T	V _{CE} = -10V , I _C =-0.5A		60		MHZ